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Amend C  
y. Robinson  
5/9/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI et al. ) Group Art Unit: 2811  
Serial No. 09/535,015 ) Examiner: S. Crane  
Filed: March 24, 2000 )  
For: METHOD OF MANUFACTURING )  
A SEMICONDUCTOR DEVICE )

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on February 24, 2003.

Adele M. Stamper

AMENDMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated October 23, 2002, please amend the above-  
identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the first and second paragraphs on page 6 with the following:

A first embodiment of the present invention is characterized in that it comprises  
steps of forming an amorphous silicon film; holding a metal element which promotes  
crystallization of silicon in contact on the surface of the amorphous silicon film; crystallizing  
the amorphous silicon film by implementing a first heat treatment to obtain a crystal silicon  
film; forming a thermal oxide film on the surface of the crystal silicon film by implementing a  
second heat treatment in the temperature range of 500° C to 700° C within an atmosphere  
containing oxygen, hydrogen and fluorine; and eliminating the thermal oxide film.

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